



Shantou Huashan Electronic Devices Co., Ltd.

PNP SILICON TRANSISTOR

HBD682

APPLICATIONS

Medium Power Linear switching.

ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$)

T_{stg} —Storage Temperature	-65~150 $^{\circ}\text{C}$
T_j —Junction Temperature	150 $^{\circ}\text{C}$
P_C —Collector Dissipation ($T_c=25^{\circ}\text{C}$)	40W
V_{CBO} —Collector-Base Voltage	-100V
V_{CEO} —Collector-Emitter Voltage	-100V
V_{EBO} —Emitter-Base Voltage	-5V
I_C —Collector Current (Pulse)	-6A
I_C —Collector Current (DC)	-4A
I_B —Base Current	-100mA

TO-126F



1 — Emitter, E
2 — Collector, C
3 — Base, B

电参数 (ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$))

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
I_{CBO}	Collector Cut-off Current			-200	μA	$V_{\text{CB}}=-100\text{V}$, $I_{\text{E}}=0$
I_{EBO}	Emitter Cut-off Current			-2	mA	$V_{\text{EB}}=-5\text{V}$, $I_{\text{C}}=0$
I_{CES}	Collector Cut-off Current			-500	μA	$V_{\text{CE}}=-100\text{V}$, $V_{\text{EB}}=0$
* H_{FE}	DC Current Gain	750				$V_{\text{CE}}=-3\text{V}$, $I_{\text{C}}=-1.5\text{mA}$
* $V_{\text{CE(sat)}}$	Collector- Emitter Saturation Voltage			-2.5	V	$I_{\text{C}}=-1.5\text{A}$, $I_{\text{B}}=-30\text{mA}$
$V_{\text{BE(on)}}$	Base-Emitter On Voltage			-2.5	V	$V_{\text{CE}}=-3\text{V}$, $I_{\text{C}}=-1.5\text{A}$
$V_{\text{CEO(sus)}}$	Collector-Emitter Sustaining Voltage	-100				$I_{\text{C}}=-50\text{mA}$, $I_{\text{B}}=0$

* Pulse Test: $PW=300\mu\text{S}$, Duty Cycle=1.5% Pulsed



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